

TENTATIVE

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS402

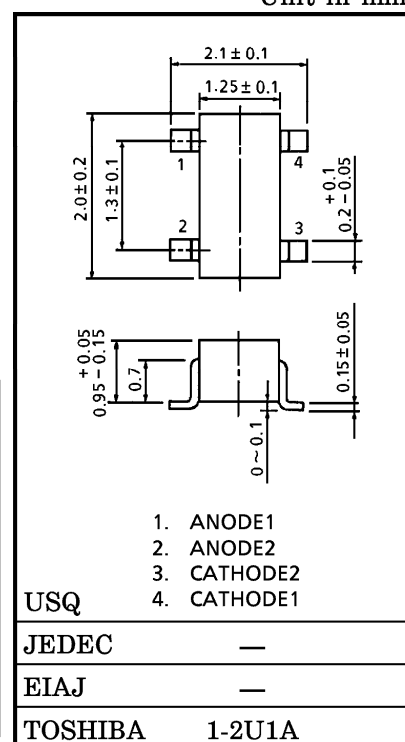
HIGH SPEED SWITCHING APPLICATIONS

Unit in mm

- Two independent diodes are mounted on four-pin ultra-small packages that are suitable for higher mounting densities.
- Low Forward Voltage : $V_F(3) = 0.50\text{ V (Typ.)}$
- Low Reverse Current : $I_R = 0.5\text{ }\mu\text{A (Max.)}$
- Small Total Capacitance : $C_T = 3.9\text{ pF (Typ.)}$

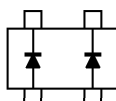
MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Maximum (Peak) Forward Current	I_{FM}	100 (*)	mA
Average Forward Current	I_O	50 (*)	mA
Surge Current (10ms)	I_{FSM}	1 (*)	A
Power Dissipation	P	100	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~125	$^\circ\text{C}$

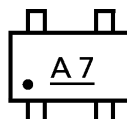
(*) Unit Rating. Total Rating = Unit Rating \times 1.5ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F(1)$	$I_F = 1\text{ mA}$	—	0.33	—	V
	$V_F(2)$	$I_F = 5\text{ mA}$	—	0.38	—	
	$V_F(3)$	$I_F = 50\text{ mA}$	—	0.50	0.55	
Reverse Current	$I_R(1)$	$V_R = 20\text{ V}$	—	—	0.5	μA
Total Capacitance	C_T	$V_R = 0, f = 1\text{ MHz}$	—	3.9	5.0	pF

PIN ASSIGNMENT (TOP VIEW)



MARKING



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